



#### **60V DUAL PNP SMALL SIGNAL TRANSISTOR IN SOT363**

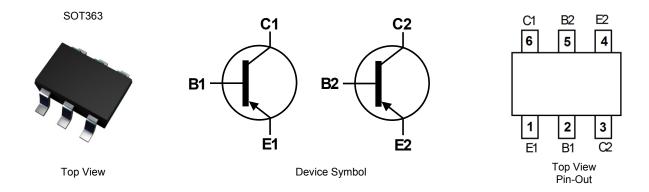
#### **Features**

- Ultra-Small Surface Mount Package
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 

   3
- Weight: 0.006 grams (approximate)



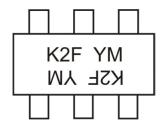
### Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMDT2907A-7-F	AEC-Q101	K2F	7	8	3,000
MMDT2907AQ-7-F	Automotive	K2F	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



K2F = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2010		2011	2012		2013	2014		2015	2016		2017
Code	Χ		Υ	Z		Α	В		С	D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Absolute Maximum Ratings (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	V
Collector Current	Ic	-600	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_{D}$	200	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

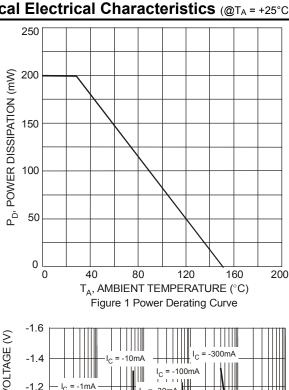
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-60	-	_	V	$I_C = -10\mu A, I_B = 0$	
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	-60	_	_	V	$I_C = -10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5		_	V	$I_E = -10\mu A, I_C = 0$	
Collector Cutoff Current	I <sub>CBO</sub>	_		-10	nA	$V_{CB} = -50V, I_{E} = 0$	
	ICBO	_	_	-10	μΑ	$V_{CB} = -50V, I_{E} = 0, T_{A} = +125^{\circ}C$	
Collector Cutoff Current	ICEX	_	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$	
Base Cutoff Current	I <sub>BL</sub>	_	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -0.5V$	
ON CHARACTERISTICS (Note 7)							
		75	_	_		$I_C = -100 \mu A$ , $V_{CE} = -10 V$	
		100	_	_		$I_C = -1.0 \text{mA}, V_{CE} = -10 \text{V}$	
DC Current Gain	h <sub>FE</sub>	100	_	_	_	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$	
		100 50	_	300	 	$I_C = -150 \text{mA}, V_{CE} = -10 \text{V}$	
		30				$I_C = -500$ mA, $V_{CE} = -10$ V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	_	-0.4	V	I <sub>C</sub> = -150mA, I <sub>B</sub> = -15mA	
				-1.6		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	-1.3 -2.6	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA	
CHALL CICNAL CHARACTERISTICS						I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA	
SMALL SIGNAL CHARACTERISTICS		1				101/5 / 0101 / 0	
Output Capacitance	C <sub>OBO</sub>	_	_	8.0	pF –	$V_{CB} = -10V, f = 1.0MHz, I_E = 0$	
Input Capacitance	C <sub>IBO</sub>	_	_	30	pF	$V_{EB} = -2.0V$ , $f = 1.0MHz$ , $I_C = 0$	
Current Gain Bandwidth Product	f⊤	200	_	_	MHz	$V_{CE} = -20V, I_{C} = -50mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS	SWITCHING CHARACTERISTICS						
Turn-On Time	t <sub>off</sub>	_	_	45	ns	V = 20\/ I- = 450 mA	
Delay Time	t <sub>d</sub>	_		10	ns	$V_{CC} = -30V$ , $I_{C} = -150$ mA, $I_{B1} = -15$ mA	
Rise Time	t <sub>r</sub>			40	ns		
Turn-Off Time	t <sub>off</sub>	_	_	100	ns	V = 6V L = 450 mA	
Storage Time	ts	_	_	80	ns	$V_{CC} = -6V$ , $I_C = -150$ mA, $I_{B1} = -I_{B2} = -15$ mA	
Fall Time	t <sub>f</sub>	_	_	30	ns	IB1IB2 13IIIA	

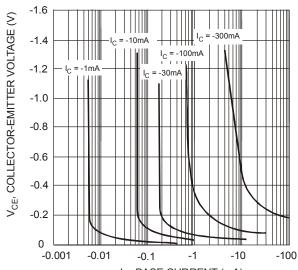
Notes: 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

7. Short duration pulse test used to minimize self-heating effect.



# Typical Electrical Characteristics (@TA = +25°C unless otherwise specified.)





I<sub>B</sub>, BASE CURRENT (mA) Fig. 3, Typical Collector Saturation Region

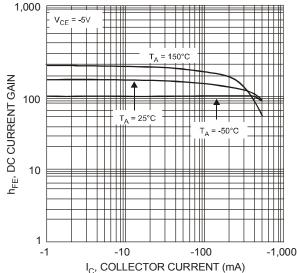


Fig. 5, DC Current Gain vs. Collector Current

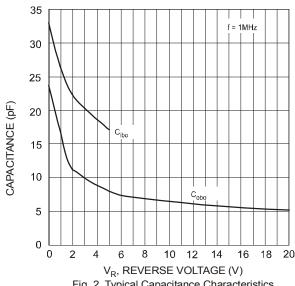


Fig. 2, Typical Capacitance Characteristics

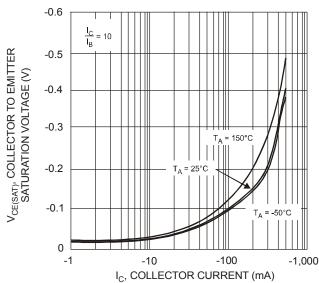
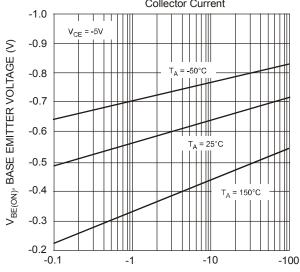
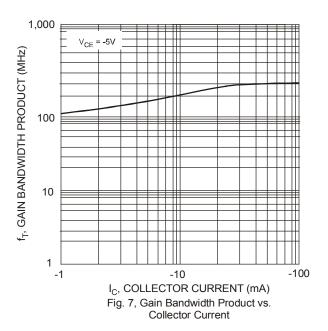


Fig. 4, Collector Emitter Saturation Voltage vs. Collector Current



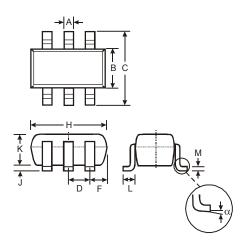
I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 6, Base Emitter Voltage vs. Collector Current





## **Package Outline Dimensions**

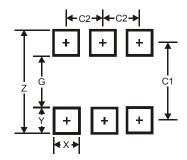
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT363						
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	0.65 Typ					
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
K	0.90	1.00	1.00			
L	0.25	0.40	0.30			
М	0.10	0.22	0.11			
α	0°	8°	-			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65



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